

(19) World Intellectual Property Organization
International Bureau



(43) International Publication Date
6 March 2008 (06.03.2008)

PCT

(10) International Publication Number
WO 2008/027143 A3

(51) International Patent Classification:
H01L 21/762 (2006.01)

(21) International Application Number:
PCT/US2007/016947

(22) International Filing Date: 27 July 2007 (27.07.2007)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
11/511,596 28 August 2006 (28.08.2006) US

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(81) Designated States (unless otherwise indicated, for every
kind of national protection available): AE, AG, AL, AM,

AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH,
CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG,
ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL,
IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK,
LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW,
MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL,
PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, SV, SY,
TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA,
ZM, ZW.

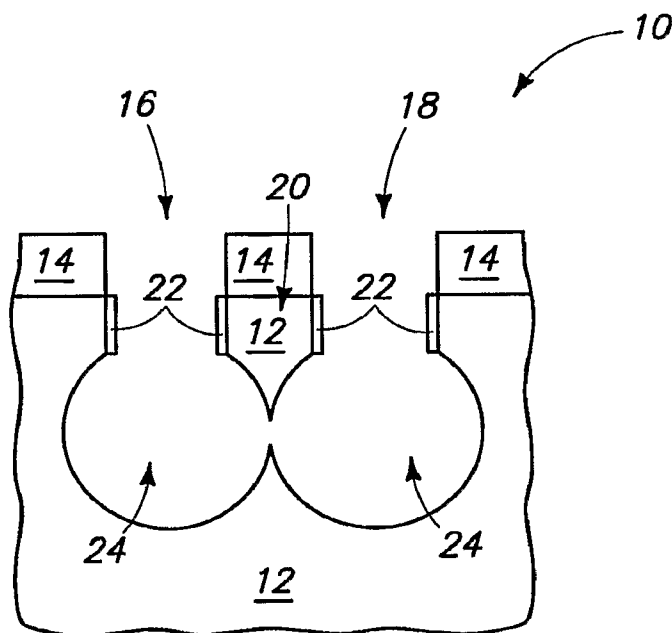
(84) Designated States (unless otherwise indicated, for every
kind of regional protection available): ARIPO (BW, GH,
GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM,
ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM),
European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI,
FR, GB, GR, HU, IE, IS, IT, LT, LU, LV, MC, MT, NL, PL,
PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM,
GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:

- with international search report
- before the expiration of the time limit for amending the
claims and to be republished in the event of receipt of
amendments

(88) Date of publication of the international search report:
24 April 2008

(54) Title: SEMICONDUCTOR DEVICES, ASSEMBLIES AND CONSTRUCTIONS, AND METHODS OF FORMING SEMI-
CONDUCTOR DEVICES, ASSEMBLIES AND CONSTRUCTIONS



(57) Abstract: Embodiments disclosed herein include methods in which a pair of openings are formed into semiconductor material, with the openings being spaced from one another by a segment of the semiconductor material. Liners are formed along sidewalls of the openings, and then semiconductor material is isotropically etched from bottoms of the openings to merge the openings and thereby completely undercut the segment of semiconductor material. Embodiments disclosed herein may be utilized in forming SOI constructions, and in forming field effect transistors having transistor gates entirely surrounding channel regions. Embodiments disclosed herein also include semiconductor constructions having transistor gates surrounding channel regions, as well as constructions in which insulative material entirely separates an upper semiconductor material from a lower semiconductor material.